

EAST-110-730534 - IIRAM Memory Cell [Electrodes.wsp:1]				25 X
File View Edit Tools Window Help				26 X
O A B C D E F G H I J K L M N O P Q R S T U V W X Y Z [\] ^ _ ` { } ~				
4				
Line	Start	Search Text	Unit	Time Stamp
23	0	((refractory same ("pt" or "Ir" or "IrO.sub.2" or "Ru" or "RuO.sub.2" or "Au" or "Ag" or "Rh" or "Pd" or "Ni" or "Co" or platinum or iridium or (iridium adj oxide) or ruthenium or (ruthenium adj oxide) or gold or silver or rhodium or palladium or nickel or cobalt)) same electrode) and (((oxygen adj blocking) or oxidation) same ("TiN" or (titanium adj nitride) or "Ta" or (tantalum adj nitride) or "TiAlN.sub.x" or (titanium adj aluminum adj nitride) or "TeAlN.sub.x" or (tantalum adj aluminum adj nitride) or "TeSiN" or (tantalum adj silicon adj nitride) or "TiSiN" or (titanium adj silicon adj nitride) or "RuTiN" or (ruthenium adj titanium adj nitride))) same electrode) and (etch or etching) and 0pd>20040722	USPAT; US-PGPUB; 2004/10/15 SPO; JPO; 14:58 DERWENT; IBM_TDB	
24	0	((refractory same ("pt" or "Ir" or "IrO.sub.2" or "Ru" or "RuO.sub.2" or "Au" or "Ag" or "Rh" or "Pd" or "Ni" or "Co" or platinum or iridium or (iridium adj oxide) or ruthenium or (ruthenium adj oxide) or gold or silver or rhodium or palladium or nickel or cobalt)) same electrode) and (((oxygen adj blocking) or oxidation) same ("TiN" or (titanium adj nitride) or "Ta" or (tantalum adj nitride) or "TiAlN.sub.x" or (titanium adj aluminum adj nitride) or "TeAlN.sub.x" or (tantalum adj aluminum adj nitride) or "TeSiN" or (tantalum adj silicon adj nitride) or "TiSiN" or (titanium adj silicon adj nitride) or "RuTiN" or (ruthenium adj titanium adj nitride))) same electrode) and (etch or etching) and 257/5.cels. and memory and 0pd>20040722	USPAT; US-PGPUB; 2004/10/15 SPO; JPO; 14:58 DERWENT; IBM_TDB	
27	0	((refractory same ("pt" or "Ir" or "IrO.sub.2" or "Ru" or "RuO.sub.2" or "Au" or "Ag" or "Rh" or "Pd" or "Ni" or "Co" or platinum or iridium or (iridium adj oxide) or ruthenium or (ruthenium adj oxide) or gold or silver or rhodium or palladium or nickel or cobalt)) same electrode) and (((oxygen adj blocking) or oxidation) same ("TiN" or (titanium adj nitride) or "Ta" or (tantalum adj nitride) or "TiAlN.sub.x" or (titanium adj aluminum adj nitride) or "TeAlN.sub.x" or (tantalum adj aluminum adj nitride) or "TeSiN" or (tantalum adj silicon adj nitride) or "TiSiN" or (titanium adj silicon adj nitride) or "RuTiN" or (ruthenium adj titanium adj nitride))) same electrode) and (etch or etching) and 257/5.cels. and memory and 0pd>20040722	USPAT; US-PGPUB; 2004/10/15 SPO; JPO; 14:58 DERWENT; IBM_TDB	
28	0	((refractory same ("pt" or "Ir" or "IrO.sub.2" or "Ru" or "RuO.sub.2" or "Au" or "Ag" or "Rh" or "Pd" or "Ni" or "Co" or platinum or iridium or (iridium adj oxide) or ruthenium or (ruthenium adj oxide) or gold or silver or rhodium or palladium or nickel or cobalt)) same electrode) same (((oxygen adj blocking) or oxidation) same ("TiN" or (titanium adj nitride) or "Ta" or (tantalum adj nitride) or "TiAlN.sub.x" or (titanium adj aluminum adj nitride) or "TeAlN.sub.x" or (tantalum adj aluminum adj nitride) or "TeSiN" or (tantalum adj silicon adj nitride) or "TiSiN" or (titanium adj silicon adj nitride) or "RuTiN" or (ruthenium adj titanium adj nitride))) same electrode) and (etch or etching) and 257/5.cels. and memory and 0pd>20040722	USPAT; US-PGPUB; 2004/10/15 SPO; JPO; 14:58 DERWENT; IBM_TDB	
29	0	((refractory same ("pt" or "Ir" or "IrO.sub.2" or "Ru" or "RuO.sub.2" or "Au" or "Ag" or "Rh" or "Pd" or "Ni" or "Co" or platinum or iridium or (iridium adj oxide) or ruthenium or (ruthenium adj oxide) or gold or silver or rhodium or palladium or nickel or cobalt)) same electrode) same (((oxygen adj blocking) or oxidation) same ("TiN" or (titanium adj nitride) or "Ta" or (tantalum adj nitride) or "TiAlN.sub.x" or (titanium adj aluminum adj nitride) or "TeAlN.sub.x" or (tantalum adj aluminum adj nitride) or "TeSiN" or (tantalum adj silicon adj nitride) or "TiSiN" or (titanium adj silicon adj nitride) or "RuTiN" or (ruthenium adj titanium adj nitride))) same electrode) and (etch or etching) and 257/44,192,296,310.cels. and memory and 0pd>20040722	USPAT; US-PGPUB; 2004/10/15 SPO; JPO; 14:58 DERWENT; IBM_TDB	
30	2	rrem and cmr and electrode and 0pd>20040722	USPAT; US-PGPUB; 2004/10/15 SPO; JPO; 14:59 DERWENT; IBM_TDB	
31	8	((refractory same ("pt" or "Ir" or "IrO.sub.2" or "Ru" or "RuO.sub.2" or "Au" or "Ag" or "Rh" or "Pd" or "Ni" or "Co" or platinum or iridium or (iridium adj oxide) or ruthenium or (ruthenium adj oxide) or gold or silver or rhodium or palladium or nickel or cobalt)) and (((oxygen adj blocking) or oxidation) same ("TiN" or (titanium adj nitride) or "Ta" or (tantalum adj nitride) or "TiAlN.sub.x" or (titanium adj aluminum adj nitride) or "TeAlN.sub.x" or (tantalum adj aluminum adj nitride) or "TeSiN" or (tantalum adj silicon adj nitride) or "TiSiN" or (titanium adj silicon adj nitride) or "RuTiN" or (ruthenium adj titanium adj nitride)))) and memory and 0pd>20040722	USPAT; US-PGPUB; 2004/10/15 SPO; JPO; 15:02 DERWENT; IBM_TDB	
32	14	rrem and 0pd>20040722	USPAT; US-PGPUB; 2004/10/15 SPO; JPO; 15:02 DERWENT; IBM_TDB	
23	22	((refractory same ("pt" or "Ir" or "IrO.sub.2" or "Ru" or "RuO.sub.2" or "Au" or "Ag" or "Rh" or "Pd" or "Ni" or "Co" or platinum or iridium or (iridium adj oxide) or ruthenium or (ruthenium adj oxide) or gold or silver or rhodium or palladium or nickel or cobalt)) and (((oxygen adj blocking) or oxidation) same ("TiN" or (titanium adj nitride) or "Ta" or (tantalum adj nitride) or "TiAlN.sub.x" or (titanium adj aluminum adj nitride) or "TeAlN.sub.x" or (tantalum adj aluminum adj nitride) or "TeSiN" or (tantalum adj silicon adj nitride) or "TiSiN" or (titanium adj silicon adj nitride) or "RuTiN" or (ruthenium adj titanium adj nitride)))) and memory and electrode and 0pd>20040722) (rrem and cmr and electrode and 0pd>20040722) (((refractory same ("pt" or "Ir" or "IrO.sub.2" or "Ru" or "RuO.sub.2" or	USPAT; US-PGPUB; 2004/10/15 SPO; JPO; 15:03 DERWENT; IBM_TDB	

updated EAST 10/15/04